74AHC1G126; 74AHCT1G126

Bus buffer/line driver; 3-state

Rev. 07 — 17 June 2009

Product data sheet

1. General description

74AHC1G126 and 74AHCT1G126 are high-speed Si-gate CMOS devices. They provide one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input pin (OE). A LOW at pin OE causes the output to assume a high-impedance OFF-state.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
    - HBM JESD22-A114E: exceeds 2000 V
    - MM JESD22-A115-A: exceeds 200 V
    - CDM JESD22-C101C: exceeds 1000 V
- Specified from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC1G126GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AHCT1G126GW				
74AHC1G126GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74AHCT1G126GV				
74AHC1G126GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AHCT1G126GM				
74AHC1G126GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74AHCT1G126GF				

founded by Philips

4. Marking

Table 2. Marking codes

Type number	Marking[1]
74AHC1G126GW	AN
74AHCT1G126GW	CN
74AHC1G126GV	A26
74AHCT1G126GV	C26
74AHC1G126GM	AN
74AHCT1G126GM	CN
74AHC1G126GF	AN
74AHCT1G126GF	CN

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

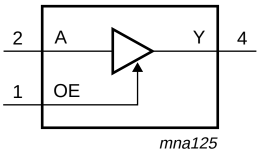


Fig 1. Logic symbol

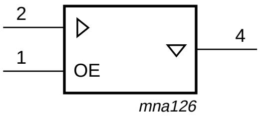


Fig 2. IEC logic symbol

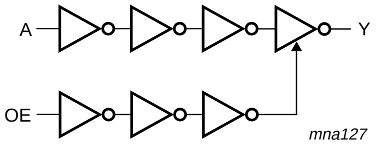


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

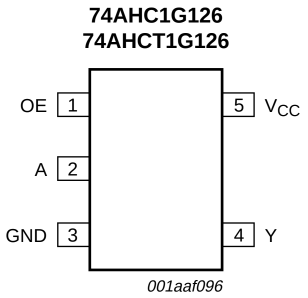


Fig 4. Pin configuration SOT353-1 and SOT753

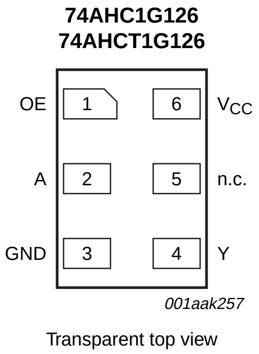


Fig 5. Pin configuration SOT886

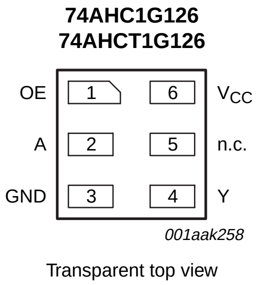


Fig 6. Pin configuration SOT891

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1/SOT753	SOT886/SOT891	
OE	1	1	output enable input
A	2	2	data input A
GND	3	3	ground (0 V)
Y	4	4	data output Y
n.c.	-	5	not connected
V_{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

Input		Output
OE	A	Y
H	L	L
H	H	H
L	X	Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
V_I	input voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1]	–20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	75	mA
I_{GND}	ground current			–75	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC1G126			74AHCT1G126			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.3 V ± 0.3 V	-	-	100	-	-	-	ns/V
		V_{CC} = 5.0 V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC1G126										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V_{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V_{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V_{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V_{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = –50 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 μA; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_O = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = 50 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_O = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10	μA
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	2.0	-	20	-	40	μA

Table 7. Static characteristics *...continued*

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_I	input capacitance		-	3	10	-	10	-	10	pF
74AHCT1G126										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = −50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = −8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10	μA
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	2.0	-	20	-	40	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; I_O = 0 A; V_{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance		-	3	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; For test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
74AHC1G126											
t_{pd}	propagation delay	A to Y; see Figure 7	[1]								
		V_{CC} = 3.0 V to 3.6 V	[2]								
		C_L = 15 pF		-	4.4	8.0	1.0	9.5	1.0	10.0	ns
		C_L = 50 pF		-	6.3	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C_L = 15 pF		-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C_L = 50 pF		-	4.7	7.5	1.0	8.5	1.0	9.5	ns

Table 8. Dynamic characteristics *…continued*
GND = 0 V; For test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{en}	enable time	OE to Y; see Figure 8 [1]								
		V_{CC} = 3.0 V to 3.6 V [2]								
		C_L = 15 pF	-	4.9	8.0	1.0	9.5	1.0	10.0	ns
		C_L = 50 pF	-	7.0	11.5	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V [3]								
		C_L = 15 pF	-	3.6	5.6	1.0	6.3	1.0	7.0	ns
		C_L = 50 pF	-	5.4	8.0	1.0	9.0	1.0	9.5	ns
t_{dis}	disable time	OE to Y; see Figure 8 [1]								
		V_{CC} = 3.0 V to 3.6 V [2]								
		C_L = 15 pF	-	6.3	9.7	1.0	11.5	1.0	12.5	ns
		C_L = 50 pF	-	9.0	13.2	1.0	15.0	1.0	16.5	ns
		V_{CC} = 4.5 V to 5.5 V [3]								
		C_L = 15 pF	-	4.3	6.8	1.0	8.0	1.0	8.5	ns
		C_L = 50 pF	-	6.1	8.8	1.0	10.0	1.0	11.0	ns
C_{PD}	power dissipation capacitance	per buffer; C_L = 50 pF; f = 1 MHz; V_I = GND to V_{CC} [4]	-	9	-	-	-	-	-	pF
74AHCT1G126										
t_{pd}	propagation delay	A to Y; see Figure 7 [1]								
		V_{CC} = 4.5 V to 5.5 V [3]								
		C_L = 15 pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C_L = 50 pF	-	4.7	7.5	1.0	8.5	1.0	9.5	ns
t_{en}	enable time	$\overline{OE}$ to Y; see Figure 8 [1]								
		V_{CC} = 4.5 V to 5.5 V [3]								
		C_L = 15 pF	-	3.4	5.6	1.0	6.3	1.0	6.5	ns
		C_L = 50 pF	-	4.8	8.0	1.0	9.0	1.0	9.0	ns
t_{dis}	disable time	$\overline{OE}$ to Y; see Figure 8 [1]								
		V_{CC} = 4.5 V to 5.5 V [3]								
		C_L = 15 pF		4.0	6.8	1.0	8.0	1.0	8.5	ns
		C_L = 50 pF		5.7	8.8	1.0	10.0	1.0	11.5	ns

Table 8. Dynamic characteristics *...continued*

GND = 0 V; For test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	per buffer; C_L = 50 pF; f = 1 MHz; V_I = GND to V_{CC}	[4]	-	11	-	-	-	-	-	pF

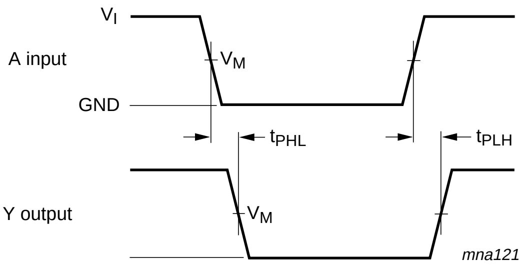
[1] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[2] Typical values are measured at V_{CC} = 3.3 V.

[3] Typical values are measured at V_{CC} = 5.0 V.

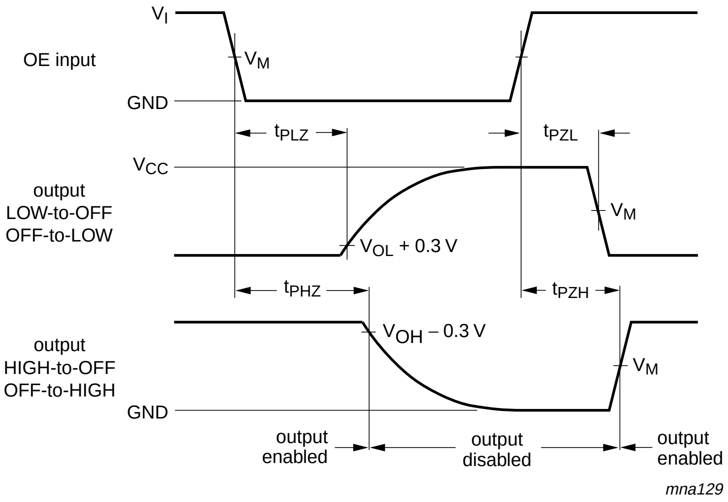
[4] C_{PD} is used to determine the dynamic power dissipation P_D (µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in Volts.

12. Waveforms



Measurement points are given in Table 9.

Fig 7. Input (A) to output (Y) propagation delays

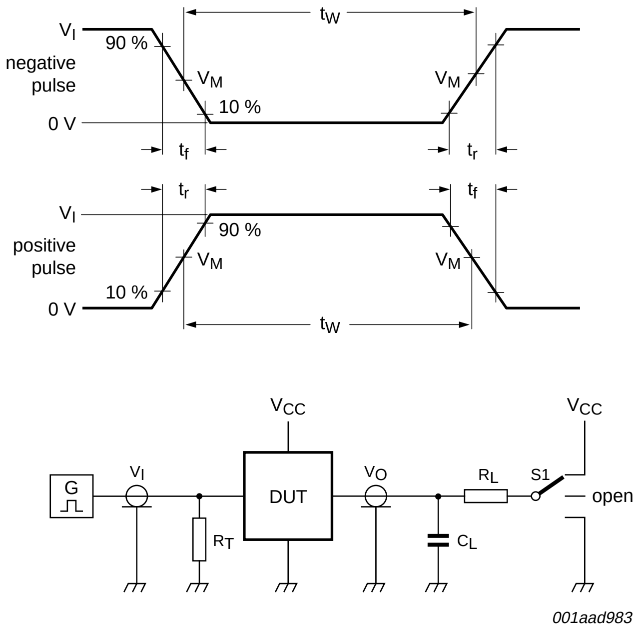


Measurement points are given in Table 9.

Fig 8. enable and disable times

Table 9. Measurement points

Type	Input		Output
	V_M	V_I	V_M
74AHC1G126	$0.5 \times V_{CC}$	GND to V_{CC}	$0.5 \times V_{CC}$
74AHCT1G126	1.5 V	GND to 3.0 V	$0.5 \times V_{CC}$



Test data is given in Table 10.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

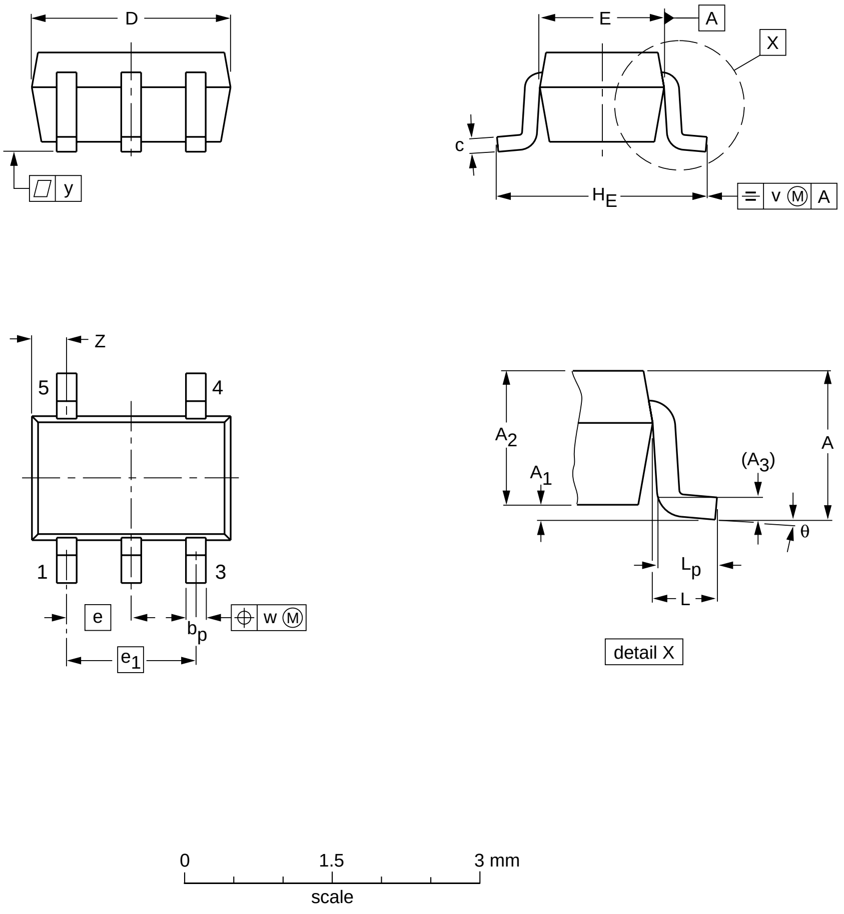
Fig 9. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC1G126	V_{CC}	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74AHCT1G126	3 V	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm **SOT353-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	e_1	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

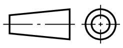
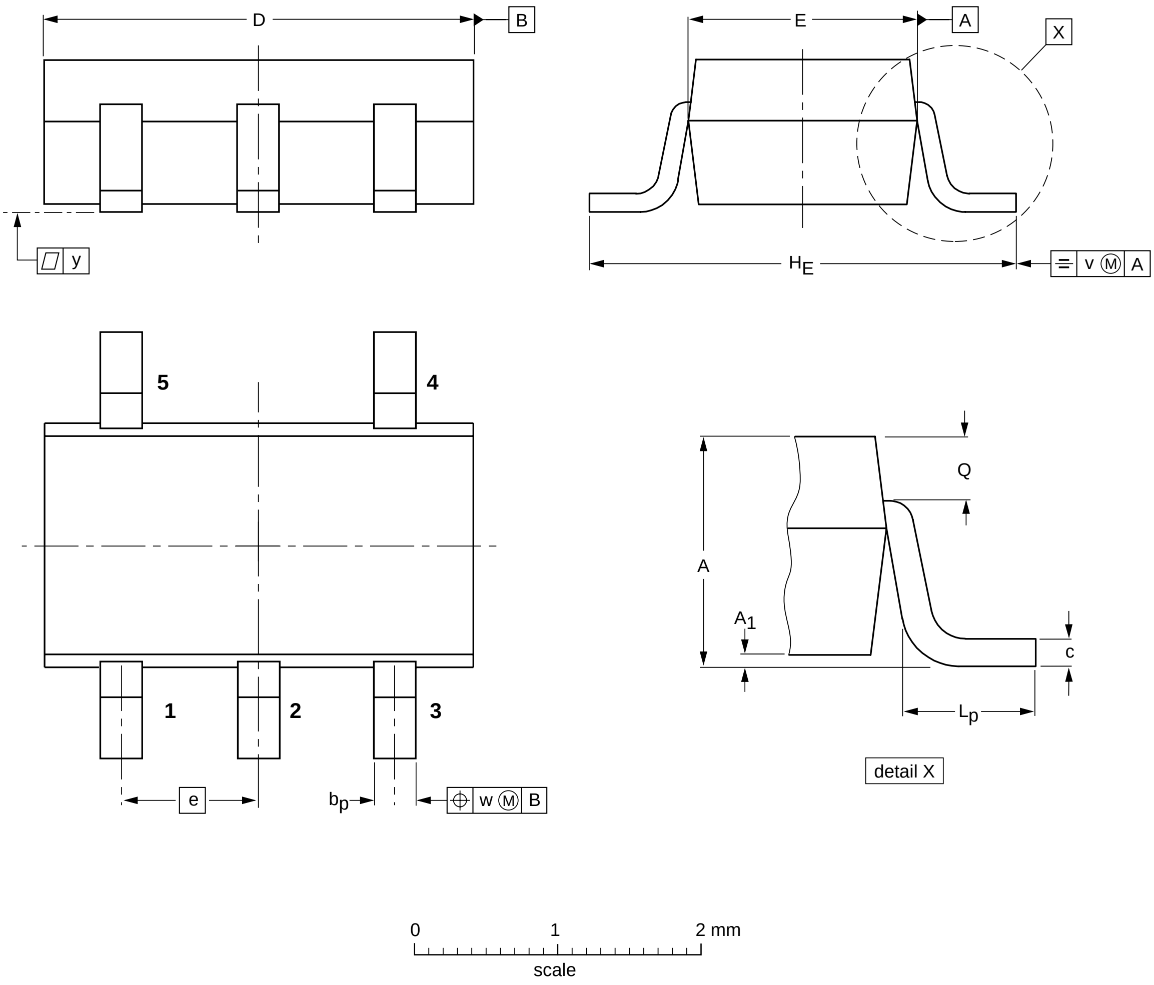
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			~~00-09-01~~ 03-02-19

Fig 10. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads **SOT753**



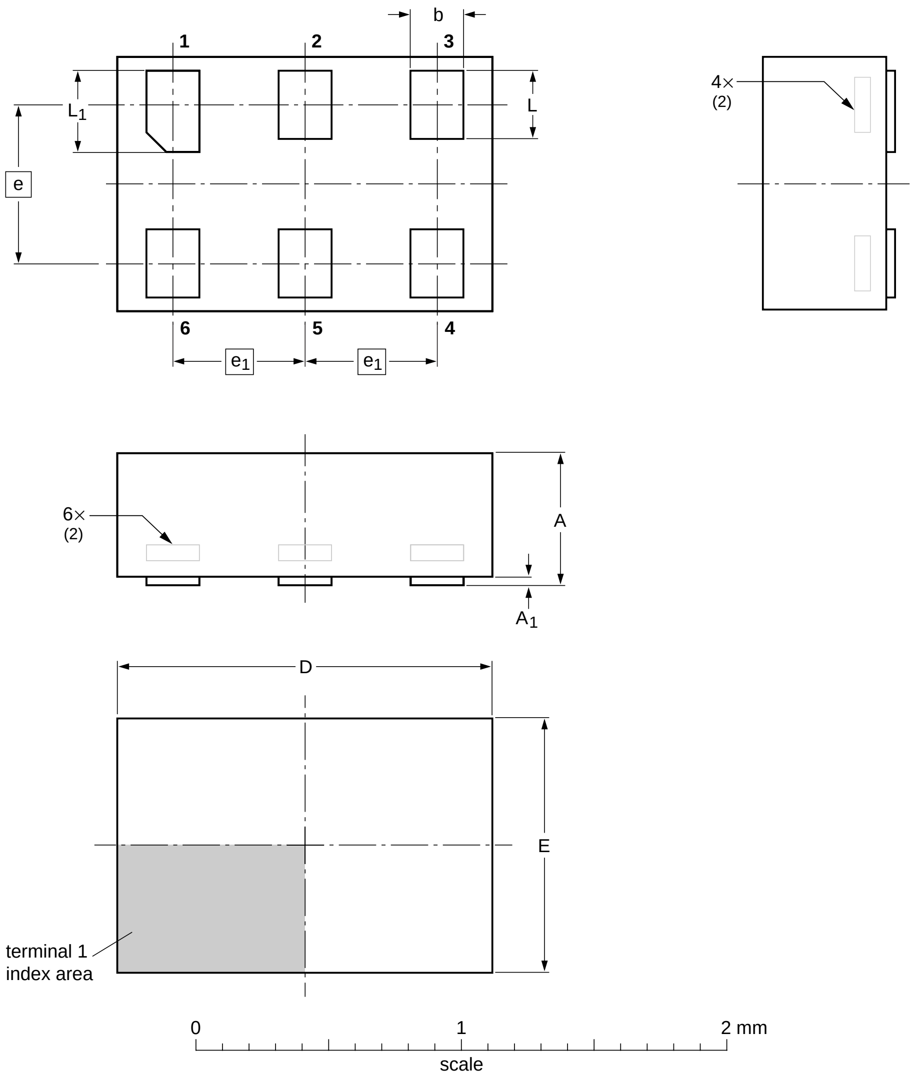
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT753			SC-74A			~~02-04-16~~ 06-03-16

Fig 11. Package outline SOT753 (SC-74A)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm **SOT886**



DIMENSIONS (mm are the original dimensions)

UNIT	$A^{(1)}$ max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.25 0.17	1.5 1.4	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

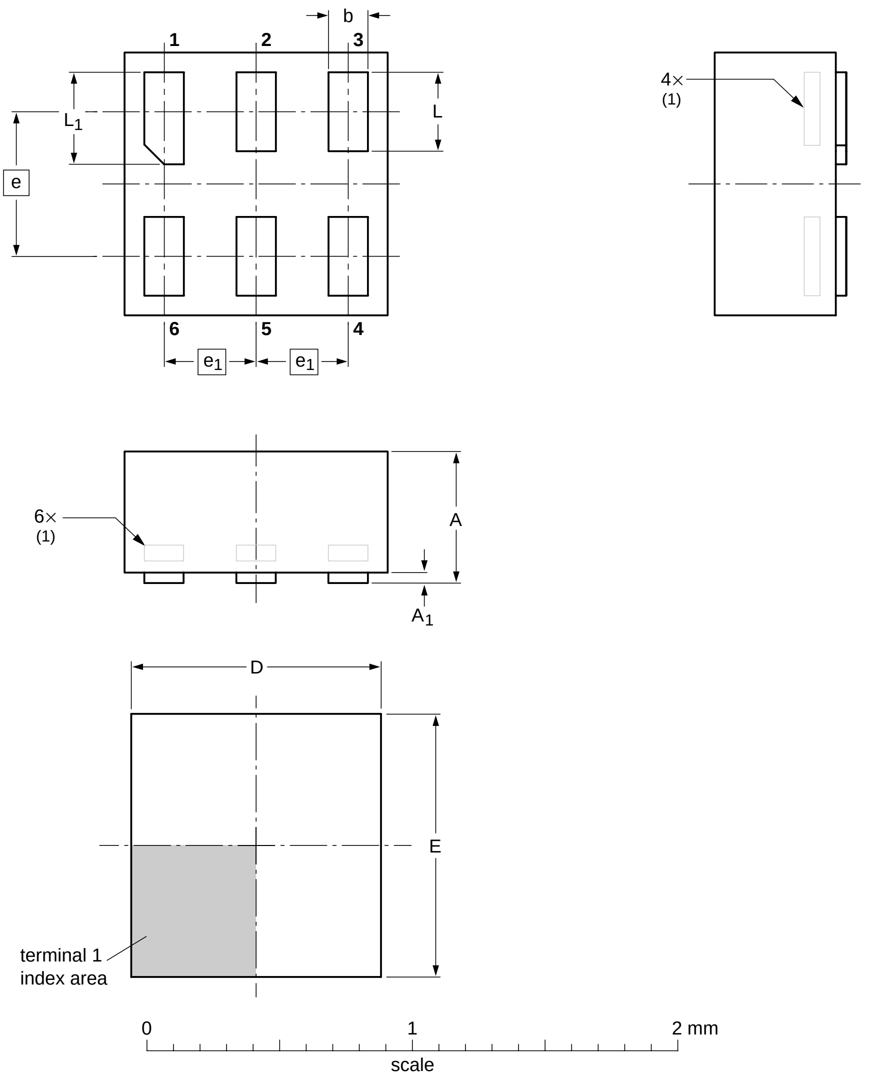
Notes

1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT886		MO-252				~~04-07-15~~ 04-07-22

Fig 12. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm **SOT891**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						~~05-04-06~~ 07-05-15

Fig 13. Package outline SOT891 (XSON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT1G126_7	20090617	Product data sheet	-	74AHC_AHCT1G126_6
Modifications:	• Package SOT886 and SOT891 added in Section 2, Section 3, Section 4, Section 6, Section 8 and Section 13.			
74AHC_AHCT1G126_6	20070525	Product data sheet	-	74AHC_AHCT1G126_5
74AHC_AHCT1G126_5	20070514	Product data sheet	-	74AHC_AHCT1G126_4
74AHC_AHCT1G126_4	20020606	Product specification	-	74AHC_AHCT1G126_3
74AHC_AHCT1G126_3	20020215	Product specification	-	74AHC_AHCT1G126_2
74AHC_AHCT1G126_2	20010406	Product specification	-	74AHC1G_AHCT1G126_1
74AHC1G_AHCT1G126_1	19990920	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term ‘short data sheet’ is explained in section “Definitions”.

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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18. Contents

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Date of release: 17 June 2009

Document identifier: 74AHC_AHCT1G126_7